Bias Resistor Transistor

NPN Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

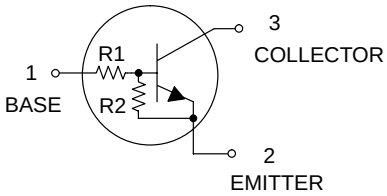
LDTC123JWT1G

- **Applications**
  Inverter, Interface, Driver

- **Features**
  1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
  2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
  3) Only the on/off conditions need to be set for operation, making the device design easy.

- We declare that the material of product compliance with RoHS requirements.

SOT–323 (SC–70)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Supply voltage	V_{CC}	50	V
Input voltage	V_{IN}	–5 to +12	V
Output current	I_O	100	mA
	$I_{C(Max.)}$	100	
Power dissipation	Pd	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

DEVICE MARKING AND RESISTOR VALUES

Device	Marking	R1 (K)	R2 (K)	Shipping
LDTC123JWT1G	N9	2.2	47	3000/Tape & Reel
LDTC123JWT3G	N9	2.2	47	10000/Tape & Reel

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	$V_{I(off)}$	–	–	0.5	V	V_{CC}=5V, I_O=100μA
	$V_{I(on)}$	1.1	–	–		V_O=0.3V, I_O=5mA
Output voltage	$V_{O(on)}$	–	0.1	0.3	V	I_O/I_I=5mA/0.25mA
Input current	I_I	–	–	3.6	mA	V_I=5V
Output current	$I_{O(off)}$	–	–	0.5	μA	V_{CC}=50V, V_I=0V
DC current gain	G_I	80	–	–	–	V_O=5V, I_O=10mA
Input resistance	R_1	1.54	2.2	2.86	kΩ	–
Resistance ratio	R_2/R_1	17	21	26	–	–
Transition frequency	f_T*	–	250	–	MHz	V_{CE}=10V, I_E= –5mA, f=100MHz

*Characteristics of built-in transistor

LDTC123JWT1G

- **Electrical characteristic curves**

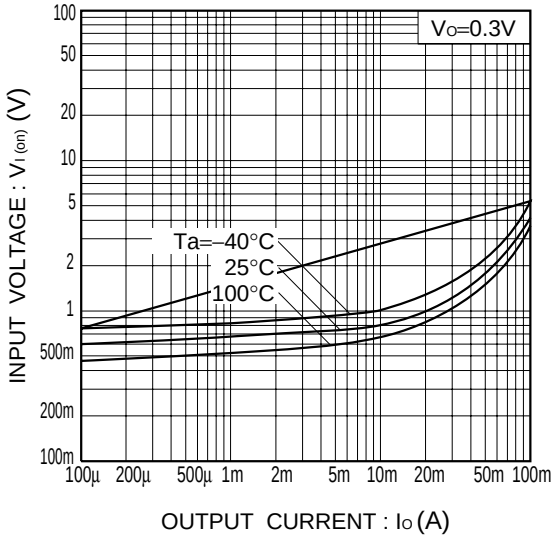


Fig.1 Input voltage vs. output current (ON characteristics)

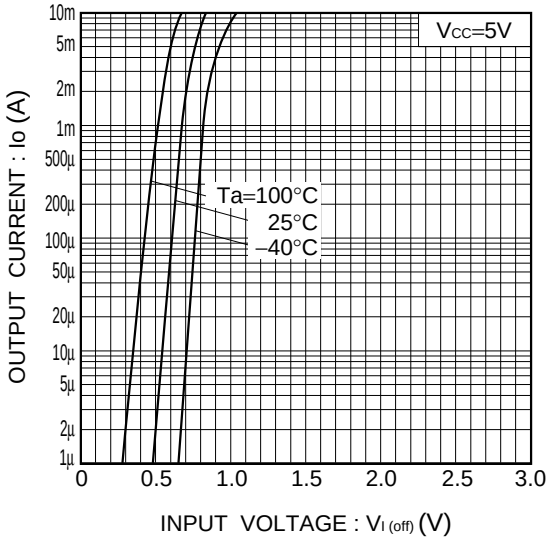


Fig.2 Output current vs. input voltage (OFF characteristics)

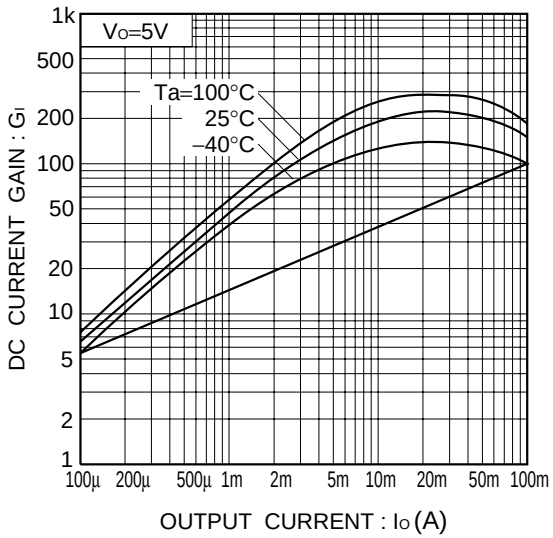


Fig.3 DC current gain vs. output current

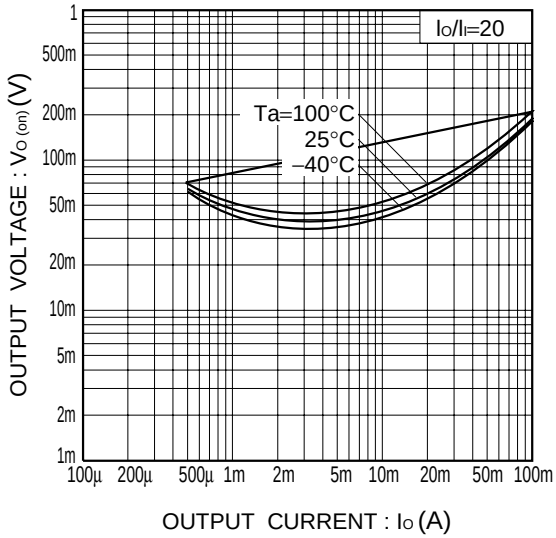
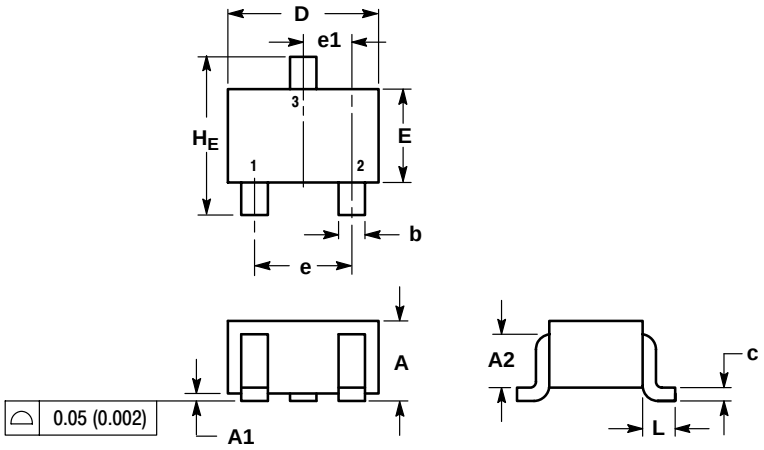


Fig.4 Output voltage vs. output current

LDTC123JWT1G

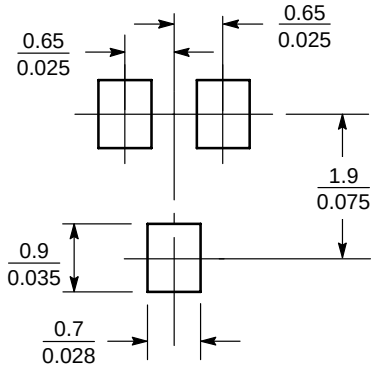
SC−70 (SOT−323)



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

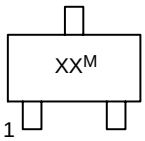
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.7 REF			0.028 REF	
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1		0.65 BSC			0.026 BSC	
L		0.425 REF			0.017 REF	
H_E	2.00	2.10	2.40	0.079	0.083	0.095

SOLDERING FOOTPRINT*



SCALE 10:1 $\left(\frac{mm}{inches}\right)$

GENERIC MARKING DIAGRAM



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.